

## Silicon Carbide Schottky Barrier Diode



#### Features

- Temperature Independent Switching Behavior
- High Surge Current Capability
- Low Conduction Loss
- Zero Reverse Recovery
- High junction temperature 175 °C
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

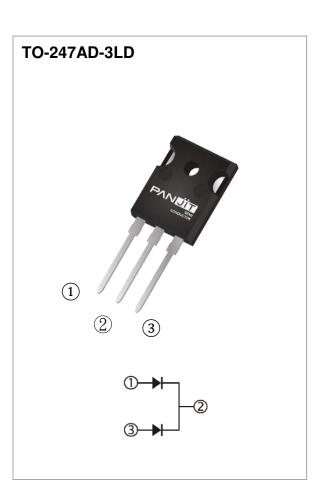
- Case: TO-247AD-3LD molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.2198 ounces, 6.231 grams

#### Application

• PFC, UPS, PV Inverter, EV Charging Station, Welder

### **Maximum Ratings and Thermal Characteristics** (T<sub>C</sub> = 25 °C unless otherwise specified)

PARAMETER			LIMIT	UNITS	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	1200	V		
DC Blocking Voltage			1200	V	
Continuous Forward Current (Per Leg/Device)	Tc= 155 ℃	IF	10 / 20	А	
Repetitive Peak Surge Current <i>Half Sine Wave, D=0.1</i> (Per Leg)	T <sub>C</sub> = 25 °C , t <sub>p</sub> =10ms T <sub>C</sub> =125 °C , t <sub>p</sub> =10ms	Ifrm	60 52	A	
Peak Forward Surge Current <i>Half Sine Wave</i> (Per Leg)	T <sub>C</sub> = 25 °C , t <sub>p</sub> =10ms T <sub>C</sub> =125 °C , t <sub>p</sub> =10ms		76 64	А	
Peak Forward Surge Current $t_p = 10us, Pulse$ (Per Leg)	IFSM	720	А		
Maximum Power Dissipation (Per Leg)	P <sub>total</sub>	164.8	W		
Operating Junction Temperature Range	TJ	-55~175	۰C		
Storage Temperature Range	Tstg	-55~175	°C		



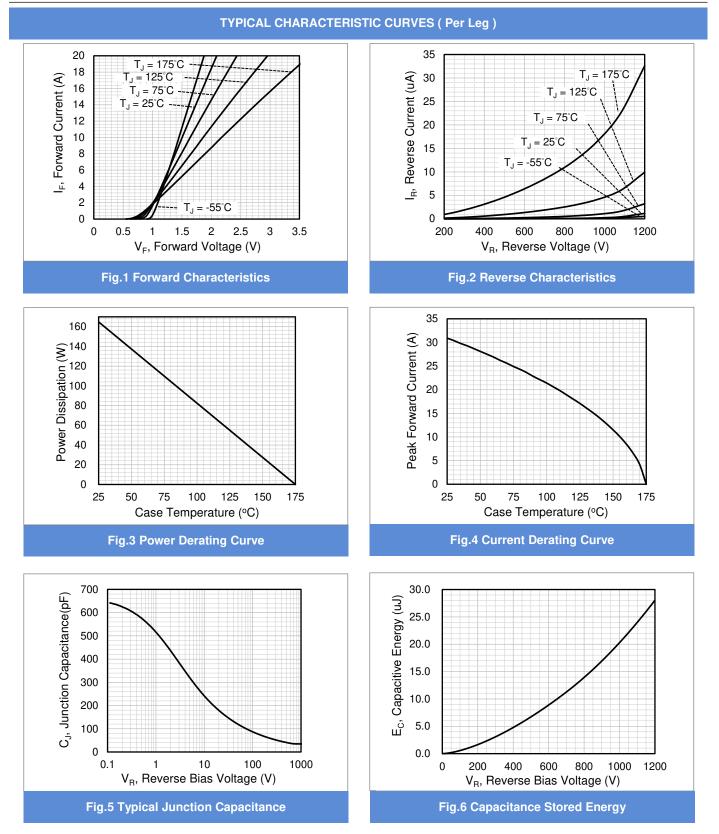


## **Electrical Characteristics** (Per Leg) ( $T_c = 25$ °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Forward Voltage Drop	VF	I <sub>F</sub> = 10 A, T <sub>J</sub> = 25 °C	-	1.5	1.7	- V	
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 175 °C	-	2.1	-		
Reverse Leakage Current	IR	$V_{R} = 1200 V, T_{J} = 25 \circ C$	-	1.16	100	μA	
		V <sub>R</sub> = 1200 V, T <sub>J</sub> = 175 °C	-	0.03	-	mA	
Total Capacitive Charge	Qc	I <sub>F</sub> = 10 A, V <sub>R</sub> = 800V	-	47.6	-	nC	
Total Capacitance	С	$V_R = 1V$ , f = 1MHz	-	516	-	рF	
		V <sub>R</sub> = 400V, f = 1MHz	-	45	-	рF	
		V <sub>R</sub> = 800V, f = 1MHz	-	35	-	рF	
Capacitance Stored Energy	Ec	V <sub>R</sub> = 800V	-	13.8	-	μJ	
Thermal Resistance	Rejc		-	0.91	-	°C/W	



# PCDH20120CCG1

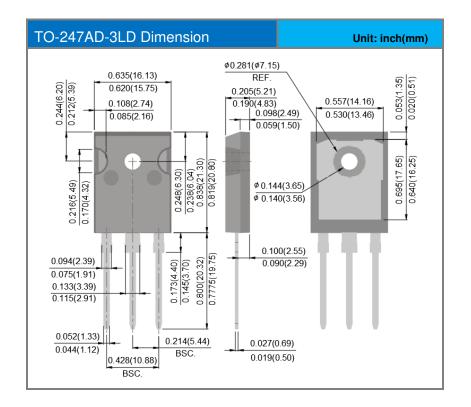




## **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PCDH20120CCG1	TO-247AD-3LD	30pcs / Tube	CDH20120CCG1

## **Packaging Information**





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